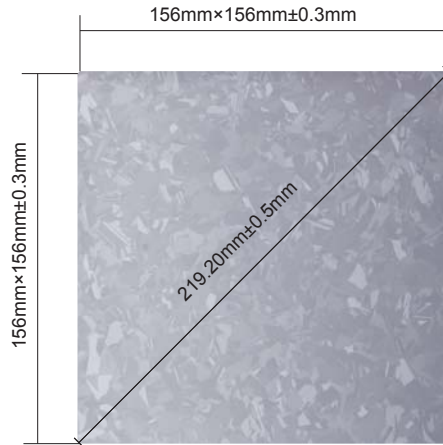


# Multicrystalline Silicon Wafer Specifications



Product	Multicrystalline Silicon Wafer
Conductivity Type	P-type
Base Area	$156.0\text{mm} \times 156.0\text{mm} \pm 0.3\text{mm}$
Diameter	$219.20\text{mm} \pm 0.5\text{mm}$
Thickness	$180\ \mu\text{m} \pm 20\ \mu\text{m}; 200\ \mu\text{m} \pm 20\ \mu\text{m}$
TTV	$\leq 30\ \mu\text{m}$
Resistivity	$0.8\text{-}3.0\ \Omega\text{cm}$
Dopant Species	Boron
Carbon Concentration	$\leq 8 \times 10^{17}\ \text{at}/\text{cm}^3$
Oxygen Concentration	$\leq 7 \times 10^{17}\ \text{at}/\text{cm}^3$
Life Time	$\geq 2\ \mu\text{s}$
Wafer Surface	As cut and cleaned.No grease stains and pin holes.
Warping	$\leq 50\ \mu\text{m}$
Corner Angle	$90 \pm 0.2\ \text{degree}$
Edge Chips	Length $\leq 1.0\text{mm}$ ,Depth $< 0.5\text{mm}$ ,No more than 2.
Edge Cracks	Not allowed
Saw Marks	Depth $\leq 15\ \mu\text{m}$
Pin Holes	No visible pin holes with naked eyes.

## Manufacture

Dexing Solar Energy Co., Ltd  
 No.300-402,RD West Jinshan, Huli Dist, Xiamen, China 361009  
 Tel:(86) 592 5237772 Fax:(86) 592 5237901  
 Email:dexing@china-dexing.com